Panni Wang

List of Publications by Year
in descending order

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25 papers	484 citations	687363 13 h-index	888059 17 g-index
25 all docs	25 docs citations	25 times ranked	557 citing authors

#	Article	IF	Citations
1	Three-Dimensional nand Flash for Vectorâ€“Matrix Multiplication. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2019, 27, 988-991.	3.1	78
2	Exploiting Hybrid Precision for Training and Inference: A 2T-1FeFET Based Analog Synaptic Weight Cell. , 2018, , .		71
3	Direct comparison of ferroelectric properties in Hf_{0.5}Zr_{0.5}O₂ between thermal and plasma-enhanced atomic layer deposition. Nanotechnology, 2020, 31, 505707.	2.6	45
4	Drain-Erase Scheme in Ferroelectric Field Effect Transistorâ€”Part II: 3-D-NAND Architecture for In-Memory Computing. IEEE Transactions on Electron Devices, 2020, 67, 962-967.	3.0	29
5	Integrated Crossbar Array With Resistive Synapses and Oscillation Neurons. IEEE Electron Device Letters, 2019, 40, 1313-1316.	3.9	26
6	Drainâ€“Erase Scheme in Ferroelectric Field-Effect Transistorâ€”Part I: Device Characterization. IEEE Transactions on Electron Devices, 2020, 67, 955-961.	3.0	26
7	Ferroelectric HfO₂-based synaptic devices: recent trends and prospects. Semiconductor Science and Technology, 2021, 36, 104001.	2.0	25
8	Cryogenic behavior of NbO2 based threshold switching devices as oscillation neurons. Applied Physics Letters, 2020, 116, .	3.3	24
9	Ferroelectric devices and circuits for neuro-inspired computing. MRS Communications, 2020, 10, 538-548.	1.8	22
10	Benchmark of Ferroelectric Transistor-Based Hybrid Precision Synapse for Neural Network Accelerator. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2019, 5, 142-150.	1.5	20
11	Investigating Ferroelectric Minor Loop Dynamics and History Effectâ€”Part I: Device Characterization. IEEE Transactions on Electron Devices, 2020, 67, 3592-3597.	3.0	18
12	Non-volatile, small-signal capacitance in ferroelectric capacitors. Applied Physics Letters, 2020, 117, .	3.3	16
13	Impact of Random Phase Distribution in Ferroelectric Transistors-Based 3-D NAND Architecture on In-Memory Computing. IEEE Transactions on Electron Devices, 2021, 68, 2543-2548.	3.0	15
14	Investigating Ferroelectric Minor Loop Dynamics and History Effectâ€”Part II: Physical Modeling and Impact on Neural Network Training. IEEE Transactions on Electron Devices, 2020, 67, 3598-3604.	3.0	15
15	The Impact of Ferroelectric FETs on Digital and Analog Circuits and Architectures. IEEE Design and Test, 2020, 37, 79-99.	1.2	13
16	Ferroelectric Tunnel Junction Optimization by Plasma-Enhanced Atomic Layer Deposition. , 2020, , .		12
17	Depolarization Field Induced Instability of Polarization States in HfO₂ Based Ferroelectric FET. , 2020, , .		11
18	Exploring argon plasma effect on ferroelectric Hf0.5Zr0.5O2 thin film atomic layer deposition. Journal of Materials Research, 2021, 36, 1206-1213.	2.6	7

#	Article	IF	Citations
19	Low Power Phase Change Memory With Vertical Carbon Nanotube Electrode. IEEE Journal of the Electron Devices Society, 2017, 5, 362-366.	2.1	5
20	Investigating Dynamic Minor Loop of Ferroelectric Capacitor. , 2019, , .		2
21	Modeling Multi-states in Ferroelectric Tunnel Junction. , 2020, , .		2
22	Ferroelectric Transistors for Synaptic Devices: Challenges and Prospects. , 2020, , .		1
23	Accelerating On-Chip Training with Ferroelectric-Based Hybrid Precision Synapse. ACM Journal on Emerging Technologies in Computing Systems, 2022, 18, 1-20.	2.3	1
24	Modeling current reduction/or PCM cell with thermal buffer layer. , 2016, , .		0
25	Exploring argon plasma effect on ferroelectric Hf_{0.5}Zr_{0.5}O₂ thin film atomic layer deposition. Journal of Materials Research, 2021, 36, 1-8.	2.6	0